Walter Meyer

List of Publications by Year
in descending order

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111	1,367	430874	395702
papers	citations	18 h-index	33 g-index

111	111	111	1166
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Electrical characterization of vapor-phase-grown single-crystal ZnO. Applied Physics Letters, 2002, 80, 1340-1342.	3.3	171
2	Determination of the mean and the homogeneous barrier height of Cu Schottky contacts on heteroepitaxial Î²â€Ga₂O₃ thin films grown by pulsed laser deposition. Physica Status Solidi (A) Applications and Materials Science, 2014, 211, 40-47.	1.8	111
3	Fabrication and characterisation of NiO/ZnO structures. Sensors and Actuators B: Chemical, 2004, 100, 270-276.	7.8	57
4	Electrical characterization of defects introduced in n-GaAs by alpha and beta irradiation from radionuclides. Applied Physics A: Solids and Surfaces, 1993, 56, 547-553.	1.4	45
5	The effect of alpha-particle and proton irradiation on the electrical and defect properties of n-GaAs. Nuclear Instruments & Methods in Physics Research B, 1994, 90, 349-353.	1.4	44
6	Summary of Schottky barrier height data on epitaxially grown n- and p-GaAs. Thin Solid Films, 1998, 325, 181-186.	1.8	40
7	Electrical characterization of defects introduced during electron beam deposition of Pd Schottky contacts on n-type Ge. Applied Physics Letters, 2006, 88, 242110.	3.3	38
8	Ti- and Fe-related charge transition levels in Î²â˜'Ga2O3. Applied Physics Letters, 2020, 116, .	3.3	37
9	Electric-field-enhanced emission and annealing behaviour of electron traps introduced in n-Si by low-energy He ion bombardment. Semiconductor Science and Technology, 1999, 14, 41-47.	2.0	35
10	The dependence of barrier height on temperature for Pd Schottky contacts on ZnO. Physica B: Condensed Matter, 2009, 404, 4402-4405.	2.7	34
11	Electrical characteristics of Ar-ion sputter induced defects in epitaxially grown n-GaAs. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1992, 10, 2366.	1.6	32
12	Electronic properties of defects in pulsed-laser deposition grown ZnO with levels at 300 and 370meV below the conduction band. Physica B: Condensed Matter, 2007, 401-402, 378-381.	2.7	30
13	Electrical characterisation of hole traps in n-type GaN. Physica Status Solidi A, 2004, 201, 2271-2276.	1.7	29
14	Effects of hydrogen, oxygen, and argon annealing on the electrical properties of ZnO and ZnO devices studied by current-voltage, deep level transient spectroscopy, and Laplace DLTS. Journal of Applied Physics, 2012, 111, 094504.	2.5	29
15	Electrical defects introduced during high-temperature irradiation of GaN and AlGaN. Physica B: Condensed Matter, 2003, 340-342, 421-425.	2.7	23
16	Electrical characterization of deep levels created by bombarding nitrogen-doped 4H-SiC with alpha-particle irradiation. Nuclear Instruments & Methods in Physics Research B, 2016, 371, 312-316.	1.4	23
17	Electrical characteristics of neutron irradiation induced defects in n-GaAs. Nuclear Instruments & Methods in Physics Research B, 1994, 90, 387-391.	1.4	18
18	Metastable-like behaviour of a sputter deposition-induced electron trap in n-GaN. Physica B: Condensed Matter, 1999, 273-274, 92-95.	2.7	18

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19	Influence (Ce and Sm) co-doping ZnO nanorods on the structural, optical and electrical properties of the fabricated Schottky diode using chemical bath deposition. Journal of Alloys and Compounds, 2019, 810, 151929.	5.5	18
20	Electronic and annealing properties of a metastable He-ion implantation induced defect in GaAs. Nuclear Instruments & Methods in Physics Research B, 1995, 106, 323-327.	1.4	17
21	Electronic and transformation properties of a metastable defect introduced inn-type GaAs by Î±-particle irradiation. Physical Review B, 1995, 51, 17521-17525.	3.2	17
22	Metal contacts to gallium arsenide. Journal of Electronic Materials, 1996, 25, 1695-1702.	2.2	17
23	Dependence of Trap Concentrations in ZnO Thin Films on Annealing Conditions. Journal of the Korean Physical Society, 2008, 53, 2861-2863.	0.7	17
24	Electric-field-enhanced emission from radiation-induced hole traps in p-GaAs. Semiconductor Science and Technology, 1995, 10, 1376-1381.	2.0	16
25	A deep level transient spectroscopy characterization of defects induced in epitaxially grown n-Si by low-energy He-ion bombardment. Journal of Applied Physics, 1998, 83, 5576-5578.	2.5	16
26	Electrical characterisation of NiO/ZnO structures. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 674-677.	0.8	15
27	Electrical characterization of defects introduced in n-type Ge during indium implantation. Applied Physics Letters, 2006, 89, 152123.	3.3	15
28	Effects of high temperature annealing on single crystal ZnO and ZnO devices. Journal of Applied Physics, 2012, 111, .	2.5	15
29	Structural, optical and electrical characteristics of nickel oxide thin films synthesised through chemical processing method. Physica B: Condensed Matter, 2018, 535, 24-28.	2.7	15
30	Effects of thermal treatment on structural, optical and electrical properties of NiO thin films. Physica B: Condensed Matter, 2019, 575, 411694.	2.7	15
31	Deep Level Transient Spectroscopy Characterization of Electron Irradiation Induced Hole Traps in p-GaAs Grown by Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 1993, 32, L974-L977.	1.5	14
32	Configurationally metastable defects in irradiated epitaxially grown boron-dopedp-type Si. Physical Review B, 2000, 63, .	3.2	13
33	A comparative study of the electrical properties of Pd/ZnO Schottky contacts fabricated using electron beam deposition and resistive/thermal evaporation techniques. Journal of Applied Physics, 2011, 110, 094504.	2.5	13
34	Electrical Characterization of High Energy Electron Irradiated Ni/4H-SiC Schottky Barrier Diodes. Journal of Electronic Materials, 2016, 45, 4177-4182.	2.2	13
35	Electrical characterization of defects introduced in Ge during electron beam deposition of different metals. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 159-161.	1.8	11
36	Metallisation induced electron traps in epitaxially grown n- type GaN. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2000, 71, 77-81.	3.5	10

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37	Electrical characterization of defects introduced during electron beam deposition of Schottky contacts on n-type Ge. Materials Science in Semiconductor Processing, 2006, 9, 576-579.	4.0	10
38	Electric Field Effect on the Emission of Electron-Irradiation-Induced Defects in n-GaAs. Japanese Journal of Applied Physics, 1994, 33, 1949-1953.	1.5	9
39	Electronic and transformation properties of a metastable defect introduced in epitaxially grown boron-doped p-type Si by alpha particle irradiation. Applied Physics Letters, 1998, 72, 3178-3180.	3.3	9
40	Bias-dependent deep level in HVPE n-GaN. Physica B: Condensed Matter, 2003, 340-342, 475-478.	2.7	9
41	Electrical characterization of defects in heavy-ion implanted n-type Ge. Nuclear Instruments & Methods in Physics Research B, 2007, 257, 169-171.	1.4	9
42	Electrical Characterization of Defects Introduced During Sputter Deposition of Schottky Contacts on n-type Ge. Journal of Electronic Materials, 2007, 36, 1604-1607.	2.2	9
43	Electrical characterization of defects introduced in nâ€Si during electron beam deposition of Pt. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 1926-1933.	1.8	9
44	A study of the T2 defect and the emission properties of the E3 deep level in annealed melt grown ZnO single crystals. Journal of Applied Physics, 2013, 113, 124502.	2.5	9
45	Ruthenium and ruthenium-based contacts to GaAs. Applied Surface Science, 1993, 70-71, 511-514.	6.1	8
46	Electrical and defect characterization of n-Type GaAs irradiated with Î±-particles using a van de graaff accelerator and an Am-241 radio-nuclide source. Physica Status Solidi A, 1993, 140, 381-390.	1.7	8
47	New electron irradiation induced electron trap in epitaxially grown Siâ€doped nâ€GaAs. Applied Physics Letters, 1995, 67, 3277-3279.	3.3	8
48	Electric Field Enhanced Emission from Two Alpha-Particle Irradiation Induced Traps in n-GaAs. Japanese Journal of Applied Physics, 1996, 35, L1-L3.	1.5	8
49	Electronic and annealing properties of the E0.31 defect introduced during Ar plasma etching of germanium. Physica B: Condensed Matter, 2009, 404, 4376-4378.	2.7	8
50	Defect introduction in Ge during inductively coupled plasma etching and Schottky barrier diode fabrication processes. Thin Solid Films, 2010, 518, 2485-2488.	1.8	8
51	Rare Earth Interstitials in Ge: A Hybrid Density Functional Theory Study. Journal of Electronic Materials, 2017, 46, 1022-1029.	2.2	8
52	Vacuum annealing characteristics of electron beam evaporated ruthenium contacts to n-GaAs grown by organometallic vapour phase epitaxy. Thin Solid Films, 1992, 213, 113-116.	1.8	7
53	Electrical characterization of He-plasma processed n-GaAs. Journal of Applied Physics, 1998, 84, 1973-1976.	2.5	7
54	Emission kinetics of electron traps introduced in n-GaN during He-ion irradiation. Nuclear Instruments & Methods in Physics Research B, 1999, 148, 474-477.	1.4	7

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55	The influence of high-energy alpha-particle irradiation on the spectral and defect properties of a Si photovoltaic detector. Semiconductor Science and Technology, 1999, 14, 323-326.	2.0	7
56	Abâ£Initio Study of Aluminium Impurity and Interstitial-Substitutional Complexes in Ge Using a Hybrid Functional (HSE). Journal of Electronic Materials, 2017, 46, 3880-3887.	2.2	7
57	Hole defects in molecular beam epitaxially grownpâ€GaAs introduced by alpha irradiation. Journal of Applied Physics, 1994, 75, 1222-1224.	2.5	6
58	Characterization of AlGaN-based metalâ€“semiconductor solar-blind UV photodiodes with IrO2 Schottky contacts. Physica B: Condensed Matter, 2012, 407, 1529-1532.	2.7	6
59	Ab initio study of metastability of Eu3+ defect complexes in GaN. Physica B: Condensed Matter, 2014, 439, 141-143.	2.7	6
60	The carbon-substitutionalâ€“carbon-interstitial (CsCi) defect pair in silicon from hybrid functional calculations. Computational Materials Science, 2016, 118, 338-341.	3.0	6
61	The influence of thermal annealing on the characteristics of Au/Ni Schottky contacts on n-type 4H-SiC. Applied Physics A: Materials Science and Processing, 2018, 124, 1.	2.3	6
62	Electrical Characterization of Metastable Defects Introduced in GaN by Eu-Ion Implantation. Materials Science Forum, 0, 679-680, 804-807.	0.3	5
63	Ar plasma induced deep levels in epitaxial n-GaAs. Journal of Applied Physics, 2012, 111, 013703.	2.5	5
64	Inductively coupled plasma induced deep levels in epitaxial n-GaAs. Physica B: Condensed Matter, 2012, 407, 1497-1500.	2.7	5
65	Introduction and annealing of primary defects in protonâ€bombarded nâ€GaN. Physica Status Solidi (B): Basic Research, 2014, 251, 211-218.	1.5	5
66	Fermi level pinning by various metal Schottky contacts on (100) OMVPE-grown n-GaAs. Thin Solid Films, 1994, 249, 95-99.	1.8	4
67	Electrical characterization of growth-induced defects inn-GaN. Radiation Effects and Defects in Solids, 2001, 156, 255-259.	1.2	4
68	Electrical characterization of defects introduced during metallization processes in n-type germanium. Materials Science in Semiconductor Processing, 2008, 11, 348-353.	4.0	4
69	Electronic properties of shallow level defects in ZnO grown by pulsed laser deposition. Journal of Physics: Conference Series, 2008, 100, 042038.	0.4	4
70	Optoelectronic characterization of Au/Ni/n-AlGaN photodiodes after annealing at different temperatures. Physica B: Condensed Matter, 2012, 407, 1628-1630.	2.7	4
71	Electrically active induced energy levels and metastability of B and N vacancy-complexes in 4Hâ€“SiC. Journal of Physics Condensed Matter, 2018, 30, 185702.	1.8	4
72	Electronic properties and defect levels induced by group III substitutionâ€“interstitial complexes in Ge. Journal of Materials Science, 2019, 54, 10798-10808.	3.7	4

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73	Modified sample holder for lowâ€temperature deepâ€level transient spectroscopy, currentâ€voltage and capacitanceâ€voltage measurements. Review of Scientific Instruments, 1992, 63, 2101-2102.	1.3	3
74	Fermi level pinning by metal Schottky contacts on n type GaAs. Materials Science and Technology, 1998, 14, 1269-1272.	1.6	3
75	Electron traps created in n-type GaN during 25 keV hydrogen implantation. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 93, 6-9.	3.5	3
76	Electrical Characterization of Defects Introduced in n-Type N-Doped 4H-SiC during Electron Beam Exposure. Solid State Phenomena, 2015, 242, 427-433.	0.3	3
77	Electrically active defects in p-type silicon after alpha-particle irradiation. Physica B: Condensed Matter, 2018, 535, 99-101.	2.7	3
78	Ab initio study of the effect of hydrogen passivation on boron-oxygen-carbon related defect complexes in silicon. Materials Science in Semiconductor Processing, 2020, 110, 104967.	4.0	3
79	Deep-level transient spectroscopy of GaN grown by electrochemical deposition and irradiated with alpha particles. Materials Science in Semiconductor Processing, 2021, 127, 105685.	4.0	3
80	Reactivation and passivation of theEc - 0.61 eV deep level in GaN. Physica Status Solidi A, 2004, 201, 2277-2280.	1.7	2
81	Laplace DLTS study of the fine structure and metastability of the radiation-induced E3 defect level in GaAs. Semiconductor Science and Technology, 2018, 33, 125011.	2.0	2
82	Effect of electron radiation on small-signal parameters of NMOS devices at mm-wave frequencies. Microelectronics Reliability, 2020, 107, 113598.	1.7	2
83	Determination of capture barrier energy of the E-center in palladium Schottky barrier diodes of antimony-doped germanium by varying the pulse width. Materials Research Express, 2020, , .	1.6	2
84	Effect of Isovalent Doping on Hydrogen Passivated Vacancy-oxygen Defect Complexes in Silicon: Insights from Density Functional Theory. Silicon, 2021, 13, 1969-1977.	3.3	2
85	DLTS study of the influence of annealing on deep level defects induced in xenon ions implanted n-type 4H-SiC. Journal of Materials Science: Materials in Electronics, 2022, 33, 15679-15688.	2.2	2
86	Effect of electron-beam deposition rate on the electrical properties of Ti/ and Pt/n-GaAs contacts. Thin Solid Films, 1993, 235, 163-168.	1.8	1
87	Electrical Characterization Of Defects Introduced During Plasma-Based Processing Of GaAs. Materials Research Society Symposia Proceedings, 1996, 442, 51.	0.1	1
88	Optical And Electrical Characterisation Study Of SICL4 Reactive Ion Etched Gaas. Materials Research Society Symposia Proceedings, 1996, 442, 75.	0.1	1
89	Electrical characterization of defects in SiCl4 plasma-etched n-GaAs and Pd Schottky diodes fabricated on it. Applied Physics Letters, 1997, 71, 668-670.	3.3	1
90	Electron emission properties of a defect at âˆ¼(Ecâˆ’0.23eV) in impurity-free disordered n-GaAs. Physica B: Condensed Matter, 2003, 340-342, 315-319.	2.7	1

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91	Field dependence of the E1â€² and M3â€² electron traps in inductively coupled Ar plasma treated n-Gallium Arsenide. Journal of Applied Physics, 2012, 111, 093703.	2.5	1
92	Comparison of two models for phonon assisted tunneling field enhanced emission from defects in Ge measured by DLTS. Physica B: Condensed Matter, 2012, 407, 1641-1644.	2.7	1
93	Observation of low-temperature annealing of a primary defect in gallium nitride. Physica B: Condensed Matter, 2014, 439, 64-66.	2.7	1
94	Properties of a previously unobserved donor-related electrically active defect in Ge induced by alpha particle irradiation. Nuclear Instruments & Methods in Physics Research B, 2017, 406, 680-682.	1.4	1
95	Electrical characterization of electron beam exposure induced defects in epitaxially grown n-type silicon. AIP Conference Proceedings, 2019, , .	0.4	1
96	First-principles Study of the Impact of Hydrogen Passivation on the Charge State Transition Levels of the CiOi(Sii)n Defect Complexes in Silicon. Silicon, 2020, 12, 2699-2704.	3.3	1
97	Electronic Properties Of Defects Formed In n-Si During Sputter-Etching In An Ar Plasma. Materials Research Society Symposia Proceedings, 1996, 442, 87.	0.1	0
98	Electrical and Optical Characterisation of Defects Induced in Epitaxially Grown n-Si During 1 keV Noble Gas Ion Bombardment. Materials Science Forum, 1997, 258-263, 565-570.	0.3	0
99	Electrical Characterization of Defects Introduced During Plasma-Based Processing of GaAs. Materials Science Forum, 1997, 258-263, 1045-1050.	0.3	0
100	Defect Formation by Low Energy Ions during Sputter Deposition of TiW and Au on Epitaxially Grown n-Si at Different Plasma Pressures. Materials Science Forum, 1997, 248-249, 249-252.	0.3	0
101	Electronic properties of defects created in epitaxially grown n-Si by low energy He and Ar ions. Nuclear Instruments & Methods in Physics Research B, 1997, 127-128, 393-396.	1.4	0
102	Characterization of a Metastable Defect Introduced In Epitaxially Grown Boron Doped Si by 5.4 Mev Î±-Particles. Materials Research Society Symposia Proceedings, 1998, 510, 449.	0.1	0
103	Defects Created by 25 keV Hydrogen Implantation in n-type GaN. Materials Research Society Symposia Proceedings, 2001, 693, 44.	0.1	0
104	Defect Engineering and Atomic Relocation Processes in Impurity-Free Disordered GaAs and AlGaAs. Materials Research Society Symposia Proceedings, 2003, 799, 1.	0.1	0
105	Effect of thermal radiation on electron emission from the E2 defect in n-GaAs. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 2333-2336.	0.8	0
106	Electrical characterization of as-grown and particle irradiated n-type bulk ZnO. , 2004, , .		0
107	Electrical Characterization of Proton Irradiated n-Type ZnO. Materials Research Society Symposia Proceedings, 2006, 957, 1.	0.1	0
108	Currentâ€“temperature measurements of a SBD evaporated onto inductively coupled plasma cleaned germanium. Physica B: Condensed Matter, 2009, 404, 4389-4392.	2.7	0

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109	Interface properties of an O2 annealed Au/Ni/n-Al0.18Ga0.82N Schottky contact. Physica B: Condensed Matter, 2012, 407, 1599-1602.	2.7	0
110	7. Metastability of the boron-vacancy complex in silicon: Insights from hybrid functional calculations. , 2018, , 113-122.		0
111	Metastability of the boron-vacancy complex in silicon: Insights from hybrid functional calculations. Physical Sciences Reviews, 2018, 3, .	0.8	0